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Kind regards,

Team Nexperia

PEMH11; PUMH11

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

Rev. 6 — 29 November 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number					Package	
	NXP JEITA complement complement		complement	configuration		
PEMH11	SOT666	-	PEMD3	PEMB11	ultra small and flat lead	
PUMH11	SOT363	SC-88	PUMD3	PUMB11	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		8.0	1	1.2	



2. Pinning information

Table 3. Pinning

Pililing		
Description	Simplified outline	Graphic symbol
GND (emitter) TR1		
input (base) TR1	6 5 4	6 5 4
output (collector) TR2		
GND (emitter) TR2		R1 R2 R2
input (base) TR2	TD1	TR1 TR2
output (collector) TR1	001aab555	R2 R1 R1 1 2 3 sym063
	Description GND (emitter) TR1 input (base) TR1 output (collector) TR2 GND (emitter) TR2 input (base) TR2	Description GND (emitter) TR1 input (base) TR1 output (collector) TR2 GND (emitter) TR2 input (base) TR2

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMH11	-	plastic surface-mounted package; 6 leads	SOT666
PUMH11	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PEMH11	H1
PUMH11	H*1

[1] * = placeholder for manufacturing site code.

5. Limiting values

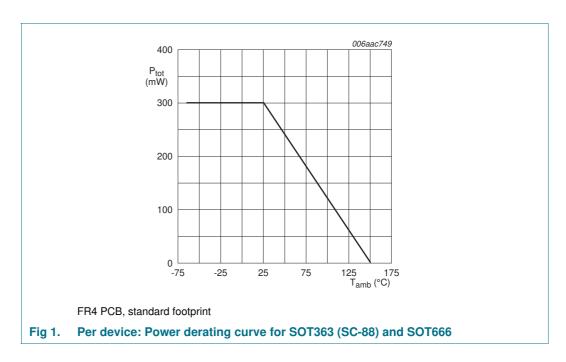
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
V_{I}	input voltage				
	positive		-	+40	V
	negative		-	-10	V
Io	output current		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1]		
	PEMH11 (SOT666)		[2] -	200	mW
	PUMH11 (SOT363)		-	200	mW
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1]		
	PEMH11 (SOT666)		[2] -	300	mW
	PUMH11 (SOT363)		-	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]			
	PEMH11 (SOT666)		[2] _	-	625	K/W
	PUMH11 (SOT363)		-	-	625	K/W
Per device	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMH11 (SOT666)		[2] _	-	417	K/W
	PUMH11 (SOT363)		-	-	417	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

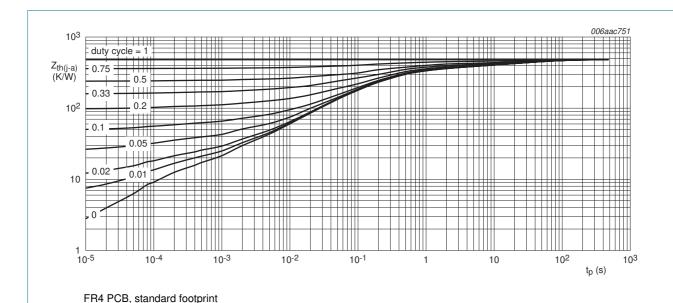


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PEMH11 (SOT666); typical values

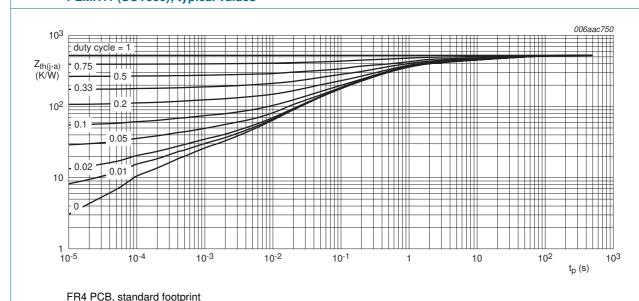


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PUMH11 (SOT363); typical values

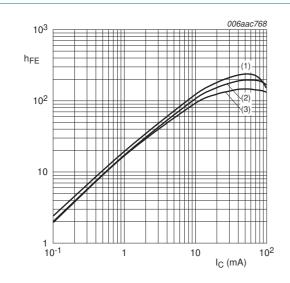
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
OLO	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	400	μА
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.1	8.0	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 10 \text{ mA}$	2.5	1.8	-	V
R1	bias resistor 1 (input)		7	10	13	$k\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CB} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	[1] -	230	-	MHz

^[1] Characteristics of built-in transistor.



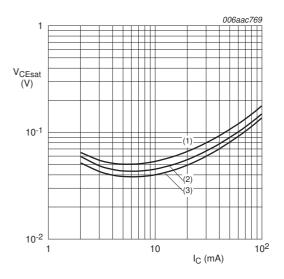
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



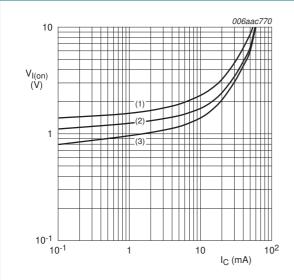
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



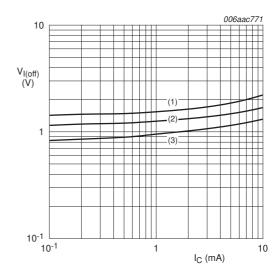
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



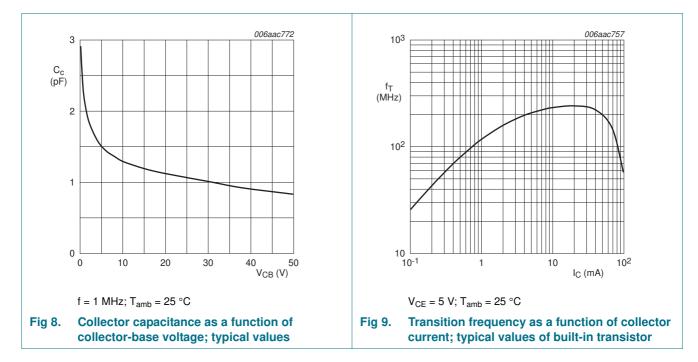
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

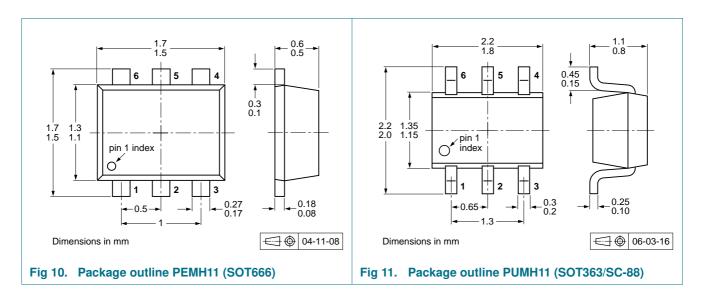


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMH11 PUMH11

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10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

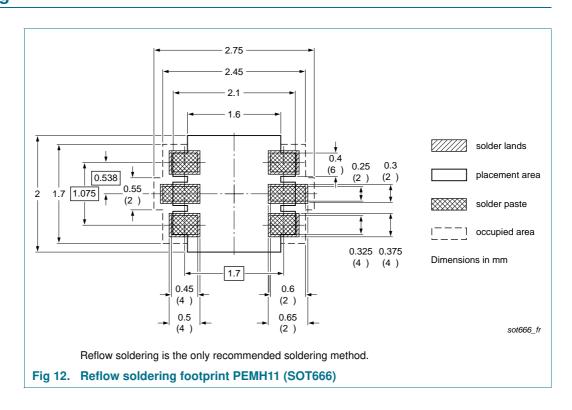
Type number	Package	Description		Packii	ng quar	ntity	
				3000	4000	8000	10000
PEMH11	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMH11	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

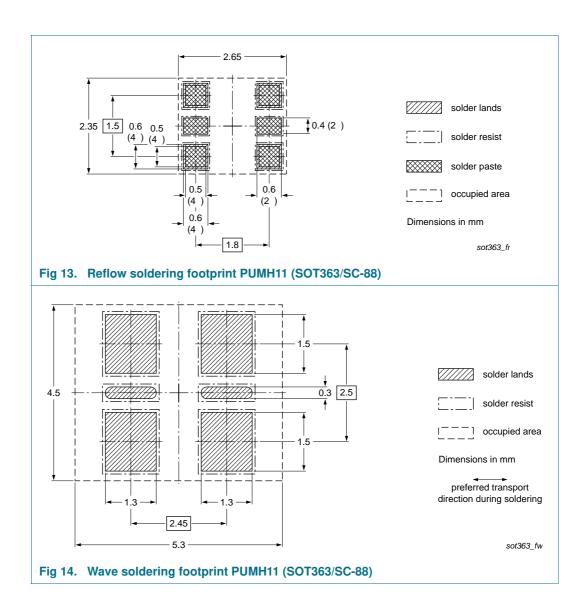
[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

11. Soldering





12. Revision history

Table 10. Revision history

,						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMH11_PUMH11 v.6	20111129	Product data sheet	-	PEMH11_PUMH11 v.5		
Modifications:		of this document has been f NXP Semiconductors.	redesigned to com	ply with the new identity		
	 Legal texts h 	nave been adapted to the r	new company name	e where appropriate.		
	 Section 1 "P 	roduct profile": updated				
	 Section 4 "N 	larking": updated				
	• <u>Table 7 "Thermal characteristics"</u> : updated according to the latest measurements					
	 <u>Table 8 "Characteristics"</u>: I_{CEO} updated according to the latest measurements, V_{i(on)} and V_{i(off)}, f_T added 					
	 Figure 1 to 9 	added :				
	 Section 8 "Telling" 	est information": added				
	 <u>Figure 10</u> and <u>11</u>: replaced by minimized package outline drawings 					
	Section 10 "	Packing information": adde	ed			
	 Section 11 "S 	Soldering": added				
	 Section 13 " 	Legal information": update	d			
PEMH11_PUMH11 v.5	20031020	Product data sheet	-	PUMH11 v.4 PEMH11 v.1		
PUMH11 v.4	19990413	Product specification	-	-		
PEMH11 v.1	20011022	Preliminary specification	-	-		

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PEMH11_PUMH11

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PEMH11; PUMH11

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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PEMH11; PUMH11

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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